(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
20 September 2001 (20.09.2001)

PCT

(10) International Publication Number
WO 01/69656 A2

(51) International Patent Classification[7]: H01L

(21) International Application Number: PCT/IB01/00392

(22) International Filing Date: 15 March 2001 (15.03.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/527,873 17 March 2000 (17.03.2000) US

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(81) Designated States *(national)*: JP, KR, SG.

(84) Designated States *(regional)*: European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR).

Published:
— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

WO 01/69656 A2

(54) Title: LOCALIZED HEATING AND COOLING OF SUBSTRATES

(57) Abstract: The present invention is directed to an apparatus and process for locally heating and/or cooling of semiconductor wafers in thermal processing chambers. In particular, the apparatus of the present invention includes a device for heating or cooling localized regions of a wafer to control the temperature of such regions during one or more stages of a heat cycle. For instance, in one embodiment, gas nozzles eject gas towards the bottom of the wafer to provide localized temperature control. In another embodiment, a transparent gas pipe containing a variety of gas outlets distributes gas onto the top surface of the wafer to provide localized temperaure control.